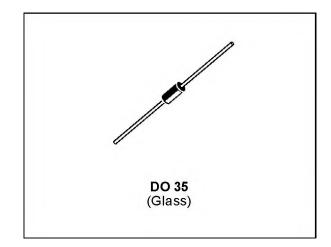


DB3 /DB4 / DC34

TRIGGER DIODES

FEATURES

V_{BO}: 32V/34V/40V VERSIONSLOW BREAKOVER CURRENT



DESCRIPTION

High reliability glass passivation insuring parameter stability and protection against junction contamination.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
Р	Power dissipation on printed circuit (L = 10 mm)	Ta = 65 °C	150	mW
I _{TRM}	Repetitive peak on-state current	tp = 20 μs F= 100 Hz	2	А
Tstg Tj	Storage and operating junction temperat	- 40 to +125 - 40 to +125	°C	

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th (j-a)}	Junction to ambient	400	°C/W
R _{th (j-l)}	Junction-leads	150	°C/W

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ELECTRICAL CHARACTERISTICS (Tj = 25°C)

Symbol	Parameter	Test Conditions		Value			Unit	
				DB3	DC34	DB4		
V _{BO}	Breakover voltage *	C = 22nF ** see diagram 1	MIN	28	30	35	V	
			TYP	32	34	40		
			MAX	36	38	45		
[I+V _{BO} I-I-V _{BO} I]	Breakover voltage symmetry	C = 22nF ** see diagram 1	MAX	± 3		V		
IΔV± I	Dynamic breakover voltage *	$\Delta I = [I_{BO} \text{ to } I_{F}=10\text{mA}]$ see diagram 1	MIN	5		V		
Vo	Output voltage *	see diagram 2	MIN	5		V		
I _{BO}	Breakover current *	C = 22nF **	MAX	100 50		100	μА	
tr	Rise time *	see diagram 3	TYP	1.5		μs		
I _B	Leakage current *	V _B = 0.5 V _{BO} max see diagram 1	MAX	10			μА	

^{*} Electrical characteristic applicable in both forward and reverse directions.

DIAGRAM 1: Current-voltage characteristics

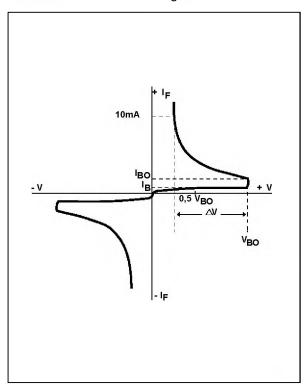


DIAGRAM 2: Test circuit for output voltage

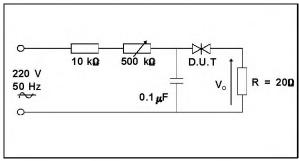
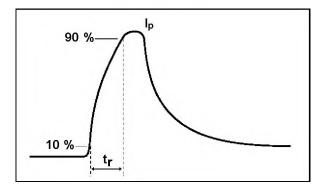


DIAGRAM 3 : Test circuit see diagram 2. Adjust R for lp=0.5A



^{**} Connected in parallel with the devices.

Fig.1: Power dissipation versus ambient temperature (maximum values)

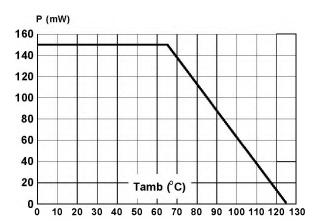


Fig.2 : Relative variation of V_{BO} versus junction temperature (typical values)

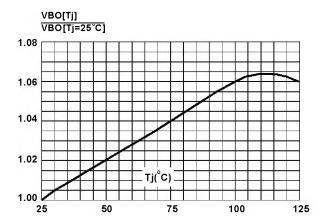
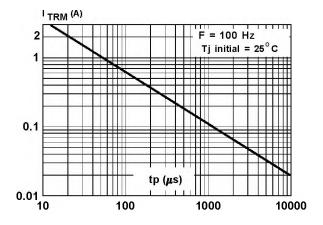
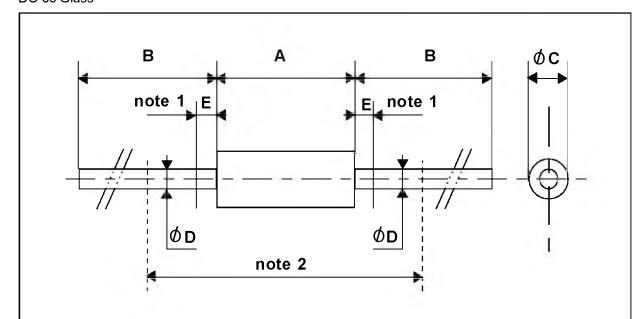


Fig.3: Peak pulse current versus pulse duration (maximum values)



PACKAGE MECHANICAL DATA (in millimeters) DO 35 Glass



REF.	DIMENSIONS				NOTES
	Millimeters Inch		hes		
	Min.	Max.	Min.	Max.	
Α	3.050	4.500	0.120	0.117	1 - The lead diameter Ø D is not_controlled over zone E
В	12.7		0.500		2 - The minimum axial lengh within which the device may be
ØC	1.530	2.000	0.060	0.079	placed with its leads bent at right angles is 0.59"(15 mm)
ØD	0.458	0.558	0.018	0.022	
E		1.27		0.050	

Cooling method by convection and conduction

Marking: type number

Weight: 0.15 g

Polarity : N A Stud torque : N A

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